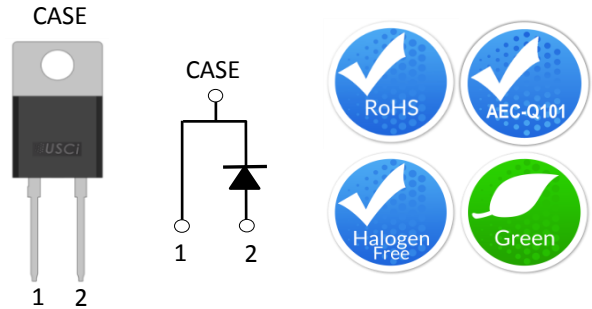


Description

United Silicon Carbide, Inc. offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D06530TS	TO-220-2L	UJ3D06530TS

Features

- ◆ 175°C maximum operating junction temperature
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ AEC-Q101 qualified

Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	V_R		650	V
Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$	V_{RRM}		650	V
Surge peak reverse voltage	V_{RSM}		650	V
Maximum DC forward current	I_F	$T_C = 140^\circ\text{C}$	30	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	165	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	150	
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	107.2	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	66.1	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	1250	A
		$T_C = 110^\circ\text{C}, t_p = 10\mu\text{s}$	1250	
Non-repetitive avalanche energy	E_{AS}	$T_j = 25^\circ\text{C}, L = 5\text{mH}, I_{pk}=9.56\text{A}, V_{DD}=100\text{V}$	254	mJ
Power dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	288.5	W
		$T_C = 140^\circ\text{C}$	67.3	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	T_J, T_{STG}		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	$^\circ\text{C}$

Electrical Characteristics

$T_J = +25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	V_F	$I_F = 30\text{A}, T_J = 25^\circ\text{C}$	-	1.5	1.7	V
		$I_F = 30\text{A}, T_J = 150^\circ\text{C}$	-	1.77	2.10	
		$I_F = 30\text{A}, T_J = 175^\circ\text{C}$	-	1.85	2.25	
Reverse current	I_R	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$	-	30	370	μA
		$V_R = 650\text{V}, T_J = 175^\circ\text{C}$	-	390		
Total capacitive charge ⁽¹⁾	Q_C	$V_R = 400\text{V}$		72		nC
Total capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$		990		pF
		$V_R = 300\text{V}, f = 1\text{MHz}$		117		
		$V_R = 600\text{V}, f = 1\text{MHz}$		101		
Capacitance stored energy	E_C	$V_R = 400\text{V}$		10.5		μJ

(1) Q_C is independent on T_J , di_F/dt , and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction - case	$R_{\theta JC}$			0.4	0.52	$^\circ\text{C}/\text{W}$

Typical Performance

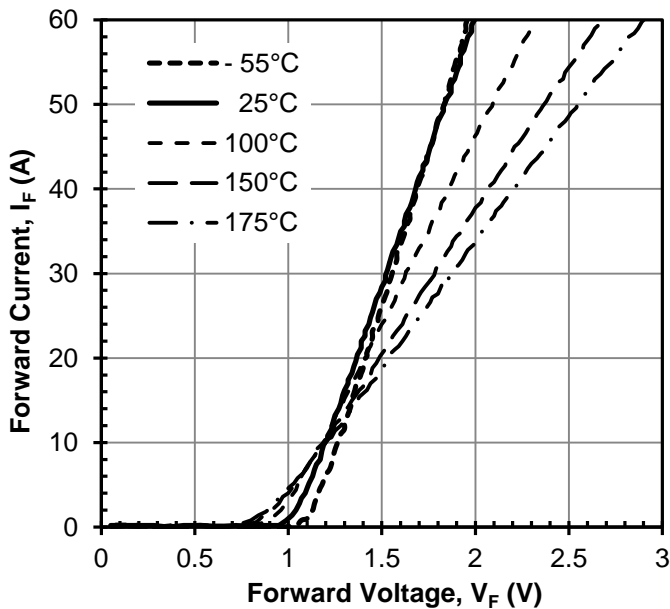


Figure 1 Typical forward characteristics

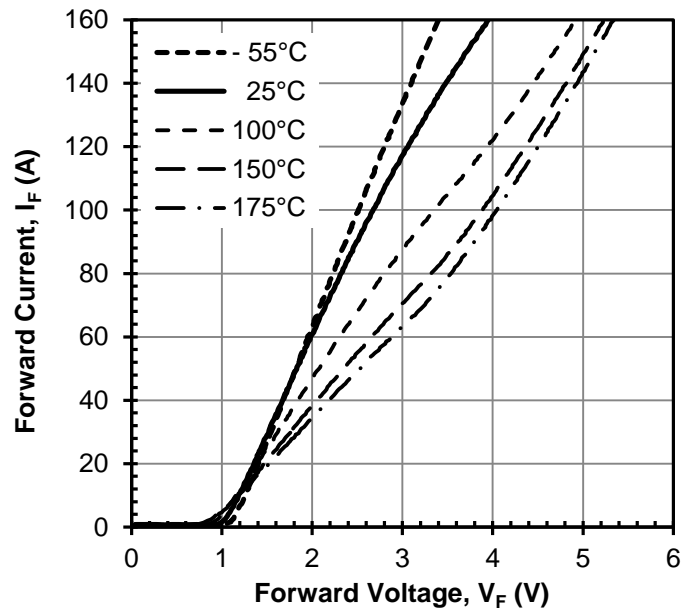


Figure 2 Typical forward characteristics in surge current

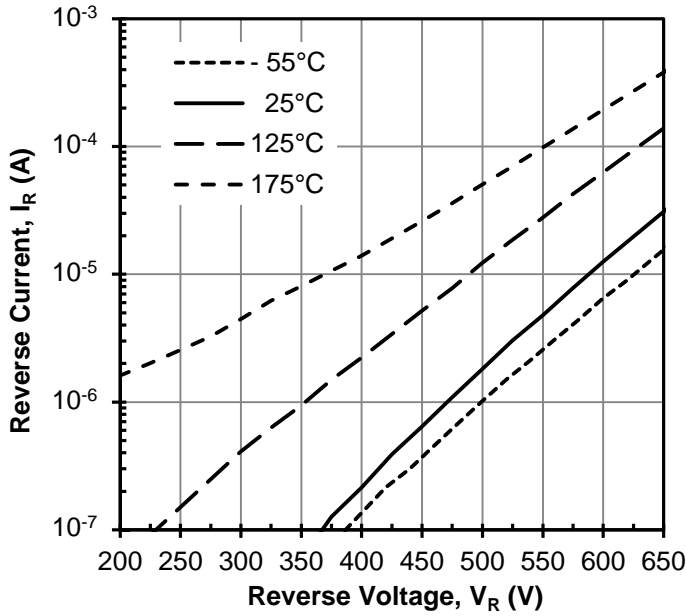


Figure 3 Typical reverse characteristics

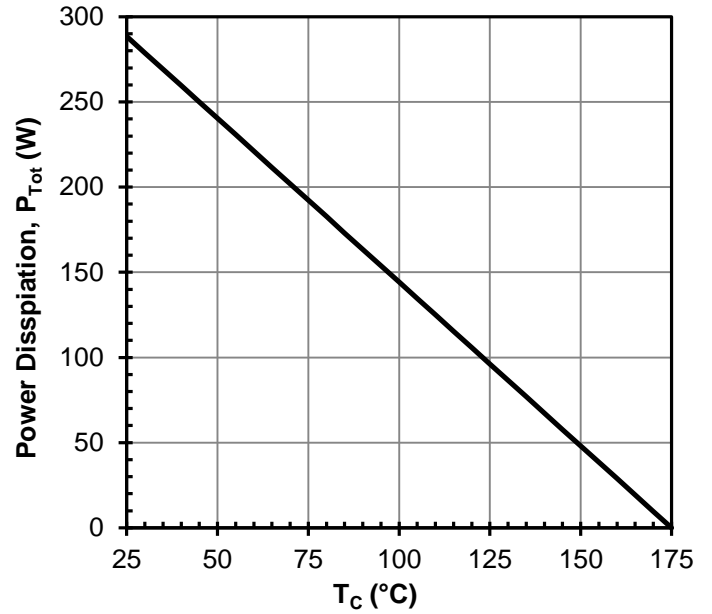


Figure 4 Power dissipation

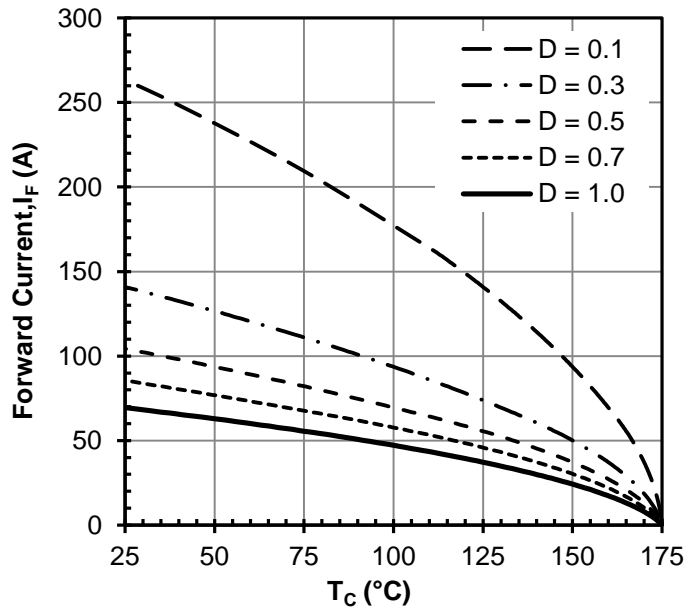


Figure 5 Diode forward current

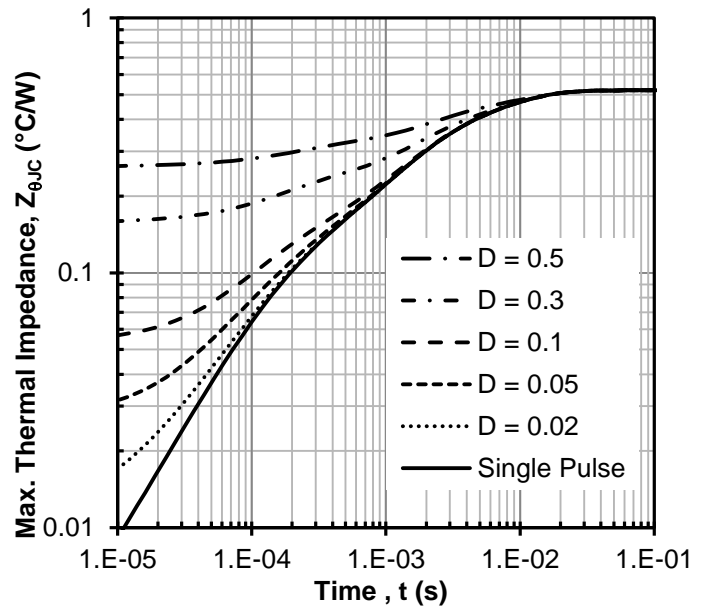


Figure 6 Maximum transient thermal impedance

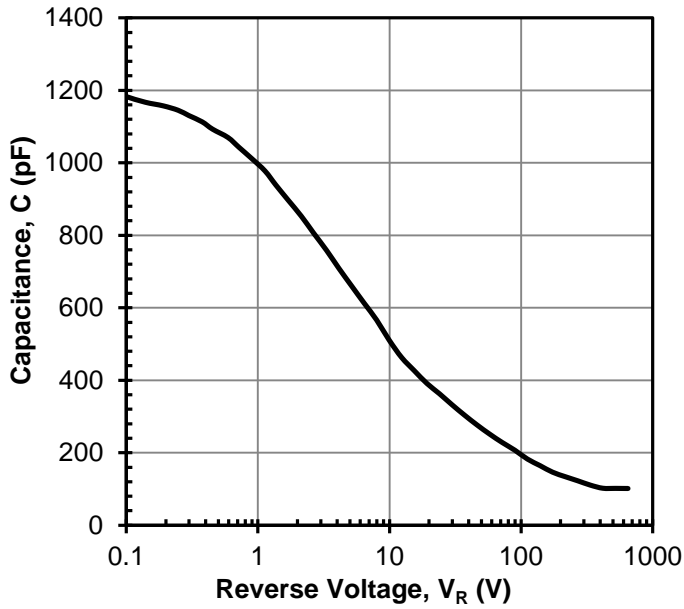


Figure 7 Capacitance vs. reverse voltage at 1MHz

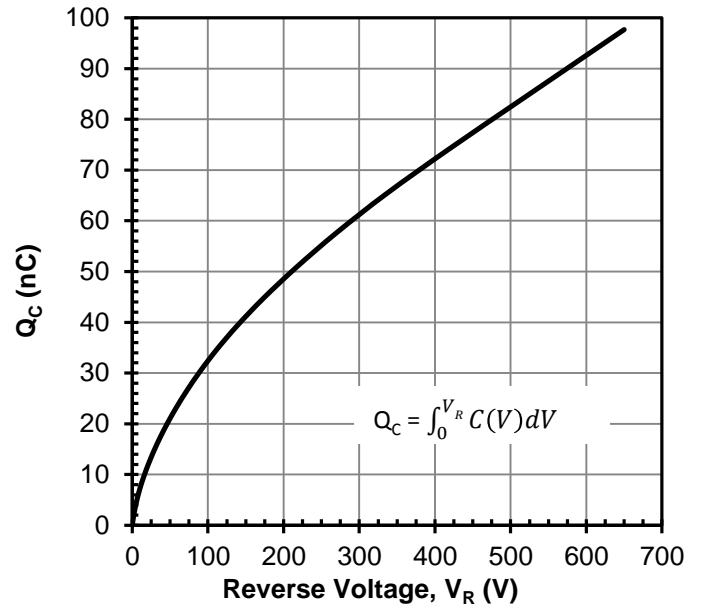


Figure 8 Typical capacitive charge vs. reverse voltage

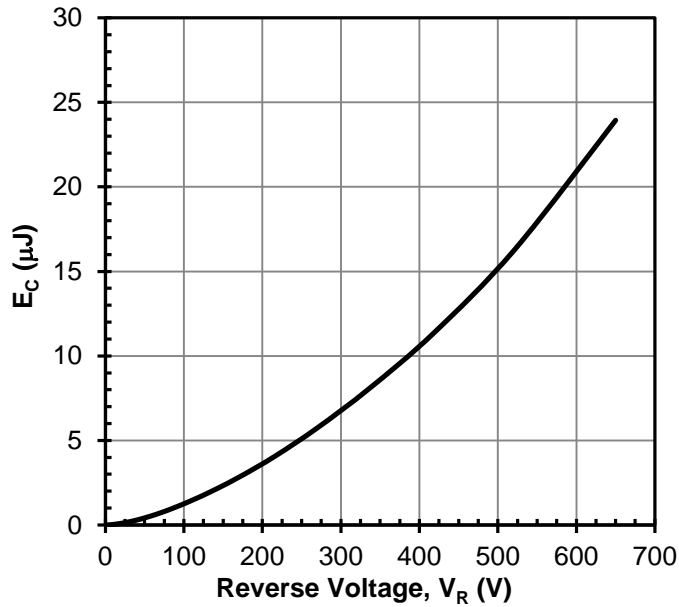


Figure 9 Typical capacitance stored energy vs. reverse voltage

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